IXYS

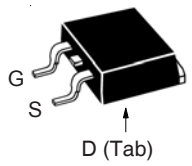
TrenchP™ Power MOSFETs

P-Channel Enhancement Mode
Avalanche Rated

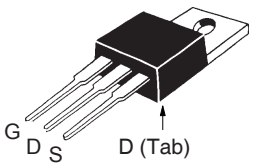
IXTA44P15T
IXTP44P15T
IXTQ44P15T
IXTH44P15T

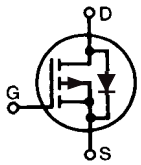
V_{DSS} = - 150V
I_{D25} = - 44A
$R_{DS(on)}$ ≤ 65mΩ

TO-263 AA (IXTA)

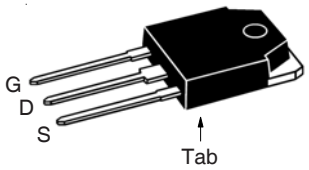


TO-220AB (IXTP)



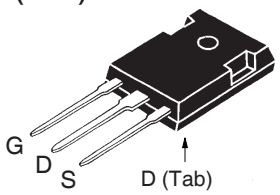


TO-3P (IXTQ)



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	T_J = 25°C to 150°C	- 150	V
V_{DGR}	T_J = 25°C to 150°C, R_{GS} = 1MΩ	- 150	V
V_{GSS}	Continuous	±15	V
V_{GSM}	Transient	±25	V
I_{D25}	T_C = 25°C	- 44	A
I_{DM}	T_C = 25°C, Pulse Width Limited by T_{JM}	-130	A
I_A	T_C = 25°C	- 22	A
E_{AS}	T_C = 25°C	1	J
P_D	T_C = 25°C	298	W
T_J		-55 ... +150	°C
T_{JM}		150	°C
T_{stg}		-55 ... +150	°C
T_L	1.6mm (0.062 in.) from Case for 10s	300	°C
T_{SOLD}	Plastic Body for 10s	260	°C
M_d	Mounting Torque (TO-220, TO-247 & TO-3P)	1.13/10	Nm/lb.in.
Weight	TO-263	2.5	g
	TO-220	3.0	g
	TO-3P	5.5	g
	TO-247	6.0	g

TO-247 (IXTH)



G = Gate D = Drain
S = Source Tab = Drain

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.	
BV_{DSS}	V_{GS} = 0V, I_D = - 250μA	-150			V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, I_D = - 250μA	- 2.0		- 4.0	V
I_{GSS}	V_{GS} = ±15V, V_{DS} = 0V			±100	nA
I_{DSS}	$V_{DS} = V_{DSS}$, V_{GS} = 0V			- 15	μA
	T_J = 125°C			- 750	μA
$R_{DS(on)}$	V_{GS} = -10V, $I_D = 0.5 \bullet I_{D25}$, Note 1			65	mΩ

Features

- International Standard Packages
- Avalanche Rated
- Extended FBSOA
- Fast Intrinsic Diode
- Low $R_{DS(ON)}$ and Q_G

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- High-Side Switching
- Push Pull Amplifiers
- DC Choppers
- Automatic Test Equipment
- Current Regulators
- Battery Charger Applications

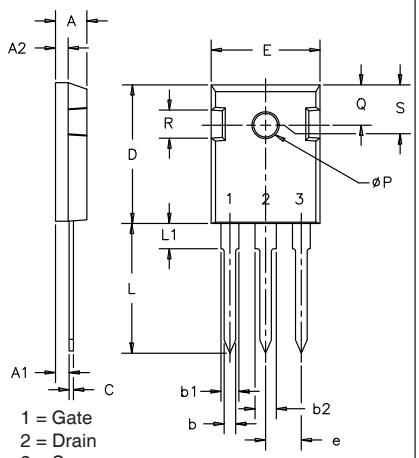
Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.
g_{fs}	V_{DS} = -10V, I_D = 0.5 • I_{D25}, Note 1	27	45	S
C_{iss}	V_{GS} = 0V, V_{DS} = - 25V, f = 1MHz		13.4	nF
C_{oss}			675	pF
C_{rss}			183	pF
$t_{d(on)}$	**Resistive Switching Times**		25	ns
t_r	V_{GS} = -10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		42	ns
$t_{d(off)}$	R_G = 1Ω (External)		50	ns
t_f			17	ns
$Q_{g(on)}$	V_{GS} = -10V, V_{DS} = 0.5 • V_{DSS}, I_D = 0.5 • I_{D25}		175	nC
Q_{gs}			65	nC
Q_{gd}			58	nC
R_{thJC}				0.42 °C/W
R_{thCS}	TO-220		0.50	°C/W
	TO-247 & TO-3P		0.21	°C/W

Source-Drain Diode

Symbol	Test Conditions (T_J = 25°C, Unless Otherwise Specified)	Characteristic Values Min.	Typ.	Max.
I_S	V_{GS} = 0V			- 44 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			-176 A
V_{SD}	I_F = I_S, V_{GS} = 0V, Note 1			-1.3 V
t_{rr}	I_F = - 22A, -di/dt = -100A/μs		140	ns
Q_{RM}	V_R = - 75V, V_{GS} = 0V		0.87	μC
I_{RM}			-12.4	A

Note 1. Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

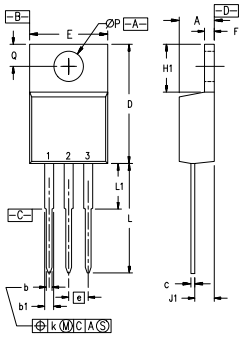
TO-247 Outline



1 = Gate
2 = Drain
3 = Source

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.209	4.7	5.3
A_1	.087	.102	2.2	2.54
A_2	.059	.098	2.2	2.6
b	.040	.055	1.0	1.4
b_1	.065	.084	1.65	2.13
b_2	.113	.123	2.87	3.12
C	.016	.031	.4	.8
D	.819	.845	20.80	21.46
E	.610	.640	15.75	16.26
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1		.177		4.50
øP	.140	.144	3.55	3.65
Q	.212	.244	5.4	6.2
R	.170	.216	4.32	5.49
S	.242 BSC		6.15 BSC	

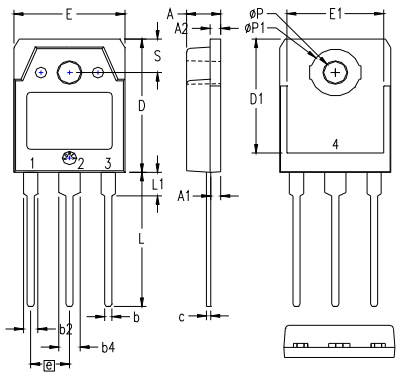
TO-220 Outline



Pins: 1 - Gate 2 - Drain
3 - Source

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.170	.190	4.32	4.83
b	.025	.040	0.64	1.02
b1	.045	.065	1.15	1.65
c	.014	.022	0.35	0.56
D	.580	.630	14.73	16.00
E	.390	.420	9.91	10.66
e	.100 BSC		2.54 BSC	
F	.045	.055	1.14	1.40
H1	.230	.270	5.85	6.85
J1	.090	.110	2.29	2.79
k	0	.015	0	0.38
L	.500	.550	12.70	13.97
L1	.110	.230	2.79	5.84
ØP	.139	.161	3.53	4.08
Q	.100	.125	2.54	3.18

TO-3P Outline

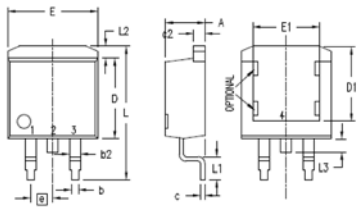


Pins: 1 - Gate 2,4 - Drain
3 - Source

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.193	4.70	4.90
A1	.051	.059	1.30	1.50
A2	.057	.065	1.45	1.65
b	.035	.045	0.90	1.15
b2	.075	.087	1.90	2.20
b4	.114	.126	2.90	3.20
c	.022	.031	0.55	0.80
D	.780	.791	19.80	20.10
D1	.665	.677	16.90	17.20
E	.610	.622	15.50	15.80
E1	.531	.539	13.50	13.70
e	.215 BSC		5.45 BSC	
L	.779	.795	19.80	20.20
L1	.134	.142	3.40	3.60
øP	.126	.134	3.20	3.40
øP1	.272	.280	6.90	7.10
S	.193	.201	4.90	5.10

All metal area are tin plated.

TO-263 Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.160	.190	4.06	4.83
A1	.080	.110	2.03	2.79
b	.020	.039	0.51	0.99
b2	.045	.055	1.14	1.40
c	.016	.029	0.40	0.74
c2	.045	.055	1.14	1.40
D	.340	.380	8.64	9.65
D1	.315	.350	8.00	8.89
E	.380	.410	9.65	10.41
E1	.245	.320	6.22	8.13
e	.100 BSC		2.54 BSC	
L	.575	.625	14.61	15.88
L1	.090	.110	2.29	2.79
L2	.040	.055	1.02	1.40
L3	.050	.070	1.27	1.78
L4	0	.005	0	0.13

Fig. 1. Output Characteristics @ T_J = 25ºC

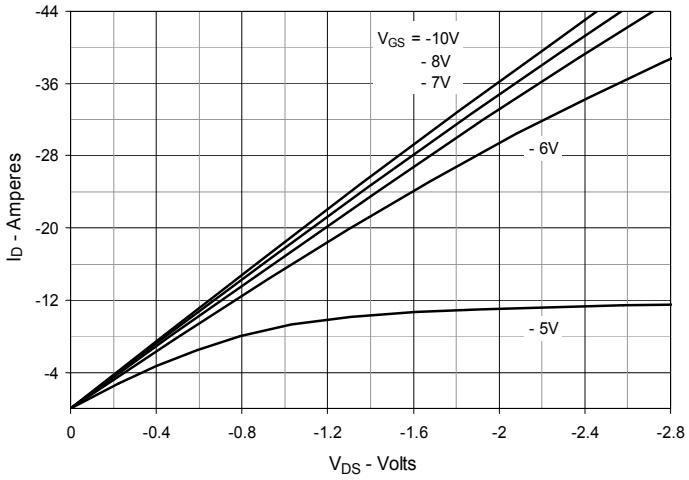


Fig. 2. Extended Output Characteristics @ T_J = 25ºC

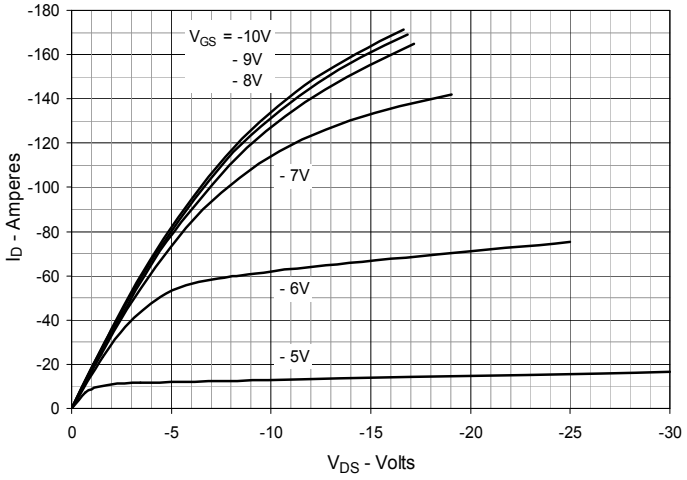


Fig. 3. Output Characteristics @ T_J = 125ºC

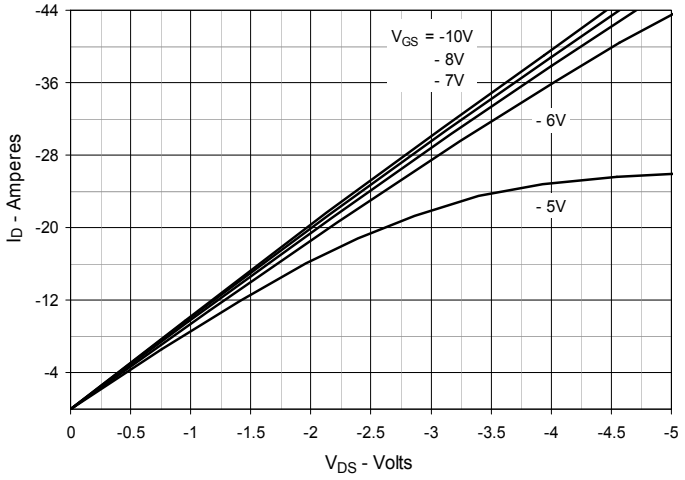


Fig. 4. $R_{DS(on)}$ Normalized to I_D = - 22A Value vs. Junction Temperature

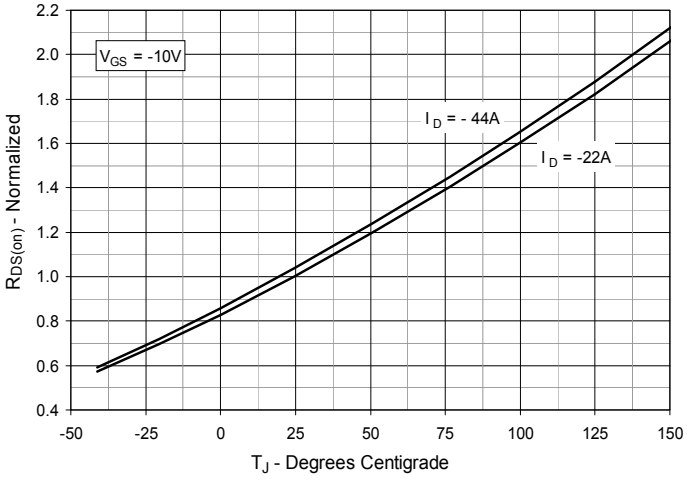


Fig. 5. $R_{DS(on)}$ Normalized to I_D = - 22A Value vs. Drain Current

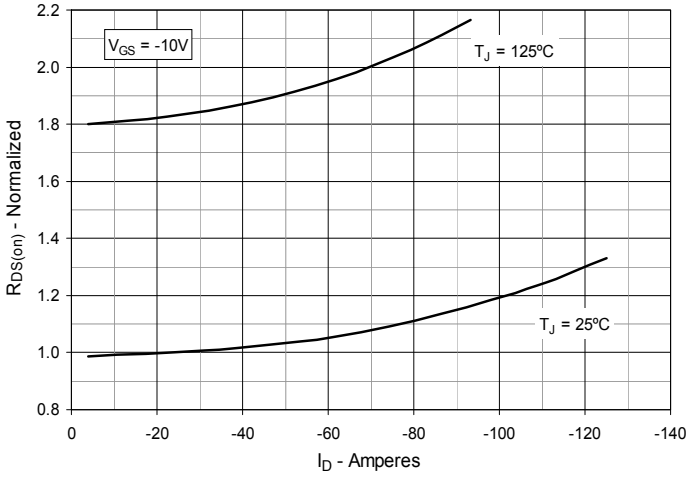


Fig. 6. Maximum Drain Current vs. Case Temperature

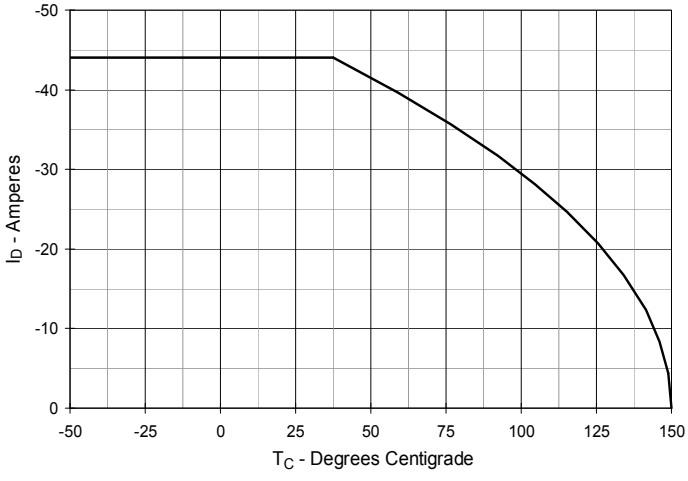


Fig. 7. Input Admittance

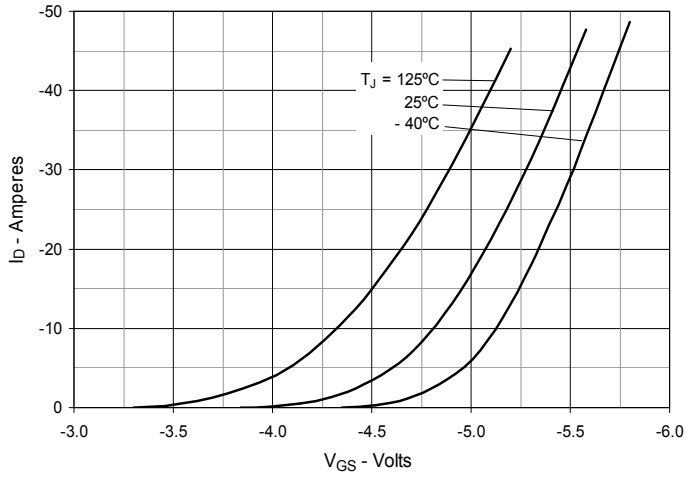


Fig. 8. Transconductance

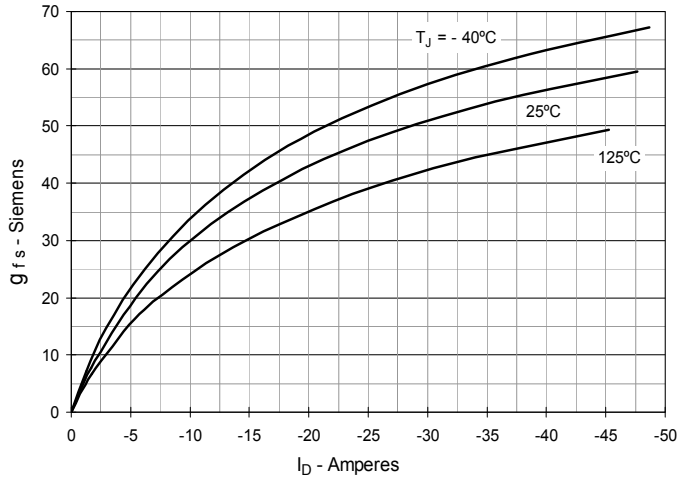


Fig. 9. Forward Voltage Drop of Intrinsic Diode

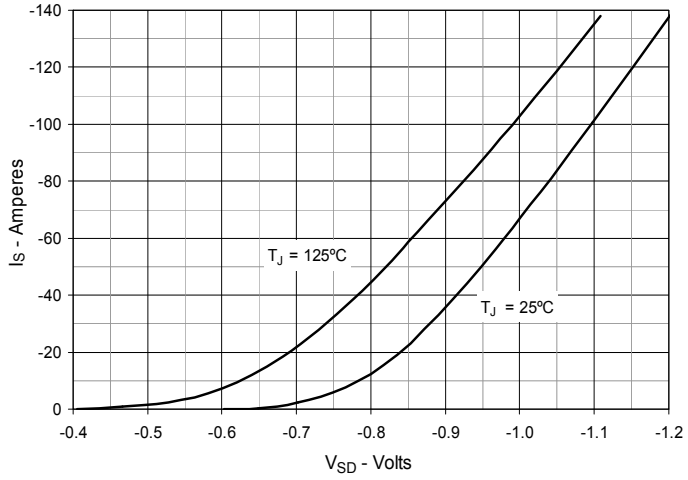


Fig. 10. Gate Charge

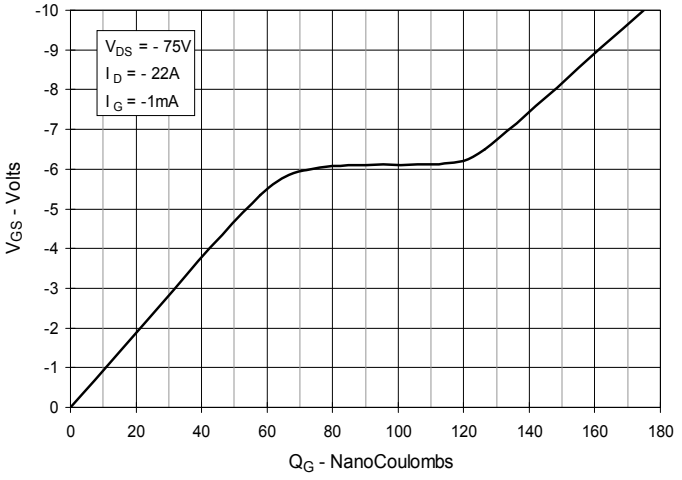


Fig. 11. Capacitance

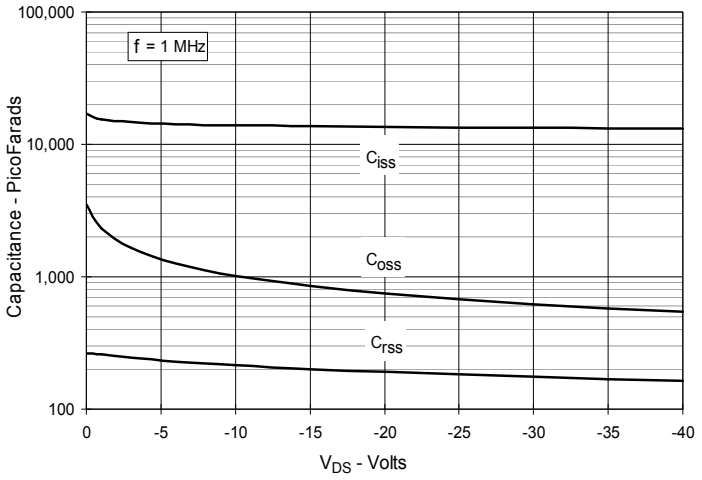


Fig. 12. Forward-Bias Safe Operating Area

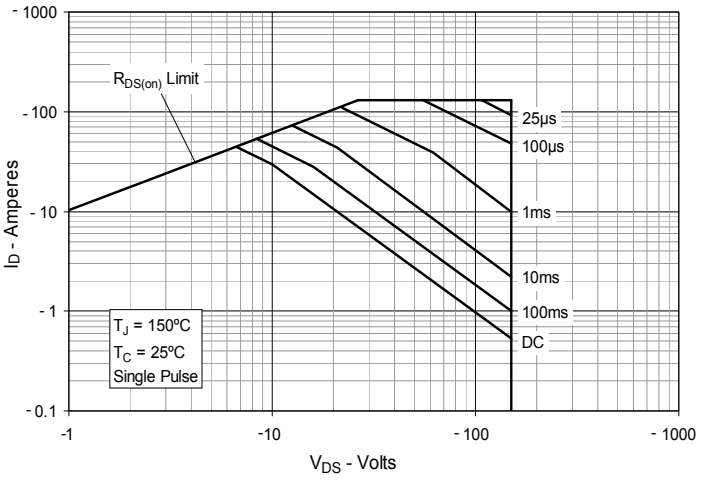


Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

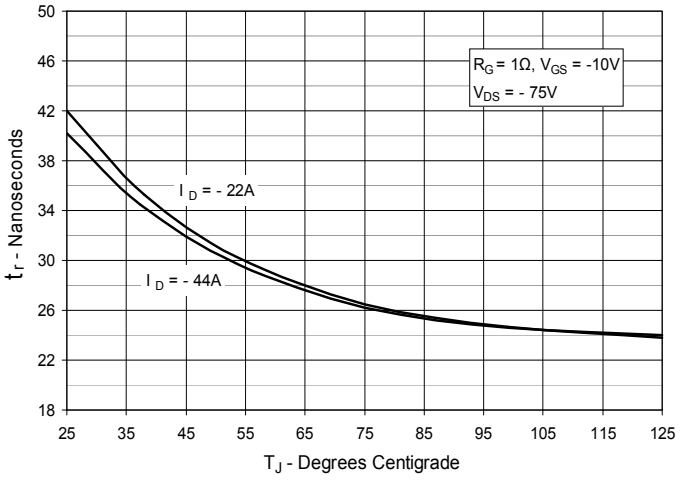


Fig. 14. Resistive Turn-on Rise Time vs. Drain Current

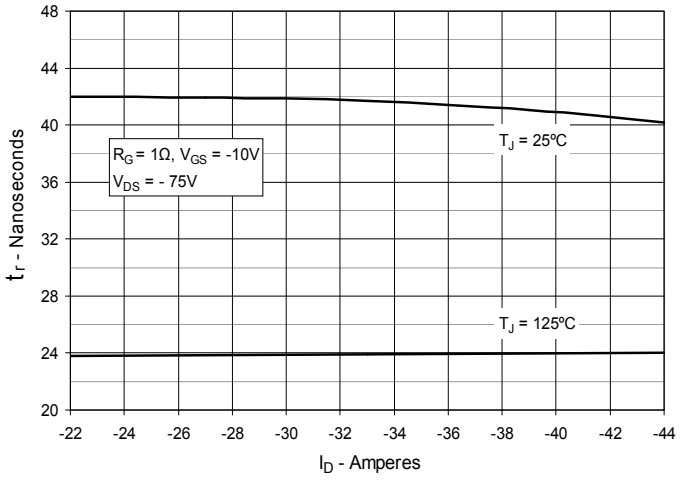


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

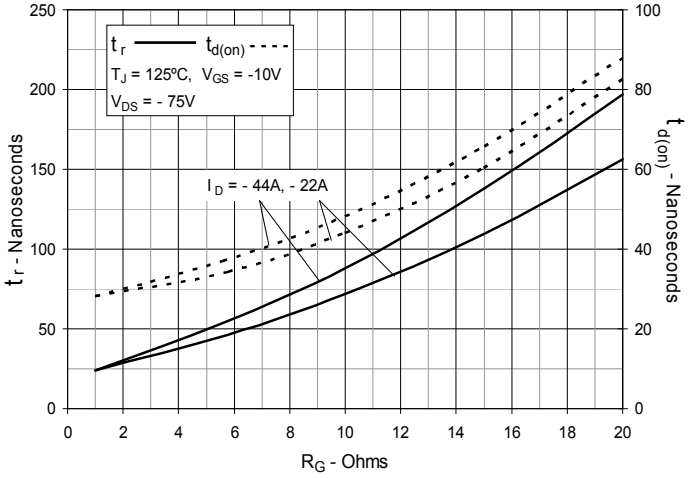


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

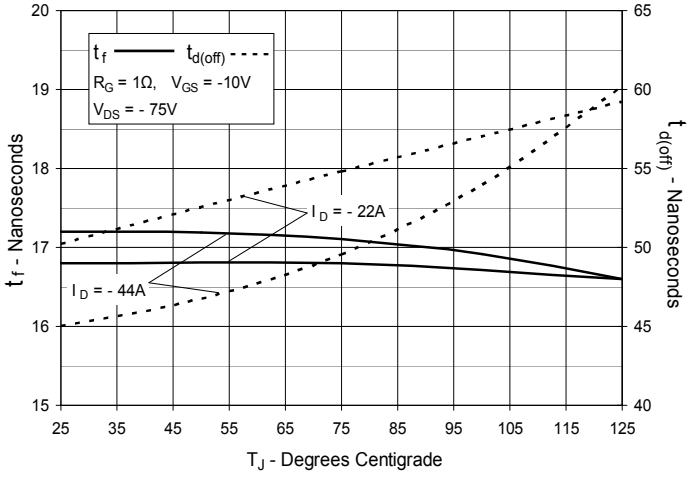


Fig. 17. Resistive Turn-off Switching Times vs. Drain Current

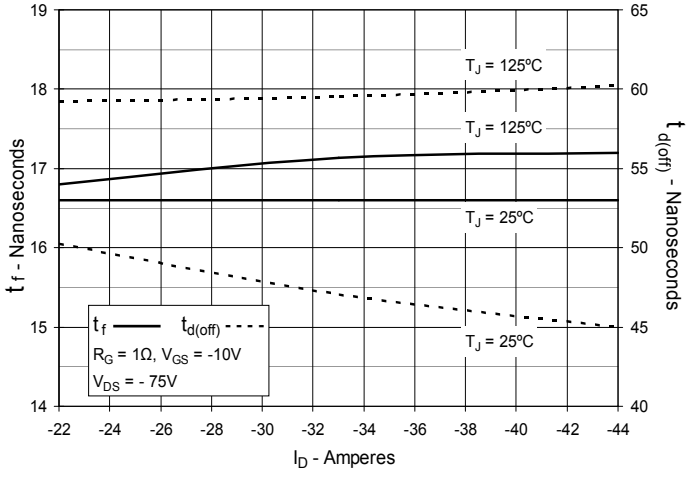


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance

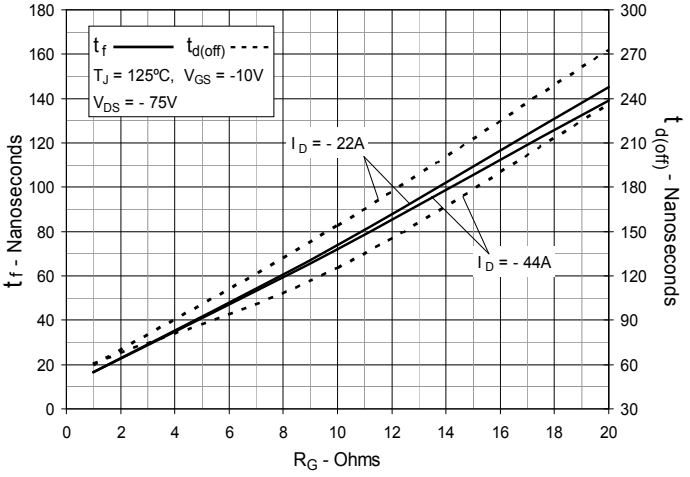


Fig. 19. Maximum Transient Thermal Impedance